BYQ28E-200E



Dual ultrafast power diodes Rev. 4 — 14 July 2011

Product data sheet

Product profile 1.

1.1 General description

Dual ultrafast power diodes in a SOT78 (TO-220AB) plastic package. These diodes are rugged with a guaranteed electrostatic discharge voltage capability.

1.2 Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state losses
- Low thermal resistance
- Soft recovery minimizes power-consuming oscillations

1.3 Applications

Output rectifiers in high-frequency switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
repetitive peak reverse voltage		-	-	200	V
average output current	square-wave pulse; $\bar{\delta} = 0.5$; $T_{mb} \le 119$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	10	Α
repetitive peak forward current	$\bar{\delta}$ = 0.5 ; t_p = 25 µs; $T_{mb} \le$ 119 °C; per diode; square-wave pulse	-	-	10	Α
acteristics					
forward voltage	$I_F = 5 \text{ A}; T_j = 150 \text{ °C};$ see Figure 4	-	8.0	0.89 5	V
naracteristics					
reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; see Figure 5	-	15	25	ns
c discharge					
electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	-	-	8	kV
	repetitive peak reverse voltage average output current repetitive peak forward current acteristics forward voltage naracteristics reverse recovery time acteristics c discharge electrostatic discharge	repetitive peak reverse voltage $ \begin{array}{ll} \text{repetitive peak reverse} \\ \text{voltage} \\ \\ \text{average output current} \\ & \text{square-wave pulse; } \delta = 0.5 \text{ ;} \\ T_{mb} \leq 119 \ ^{\circ}\text{C; both diodes} \\ \text{conducting; see } \underline{\text{Figure 1;}} \\ \text{see } \underline{\text{Figure 2}} \\ \\ \text{repetitive peak forward} \\ \text{current} \\ & \delta = 0.5 \text{ ; } t_p = 25 \ \text{µs;} \\ T_{mb} \leq 119 \ ^{\circ}\text{C; per diode;} \\ \text{square-wave pulse} \\ \\ \text{acteristics} \\ \\ \text{forward voltage} \\ & I_F = 5 \text{ A; } T_j = 150 \ ^{\circ}\text{C;} \\ \text{see } \underline{\text{Figure 4}} \\ \\ \text{haracteristics} \\ \\ \text{reverse recovery time} \\ & I_F = 1 \text{ A; } V_R = 30 \text{ V;} \\ \text{dI}_F/\text{dt} = 100 \text{ A/µs; } T_j = 25 \ ^{\circ}\text{C;} \\ \text{ramp recovery; see } \underline{\text{Figure 5}} \\ \\ \text{c discharge} \\ \\ \text{electrostatic discharge} \\ \\ \text{HBM; } C = 250 \text{ pF; } R = 1.5 \text{ k}\Omega; \\ \\ \end{array} $	repetitive peak reverse voltage $ \begin{array}{c} - \\ \text{voltage} \\ \\ \text{average output current} \\ \text{average output current} \\ \text{square-wave pulse; } \delta = 0.5 \text{ ;} \\ T_{mb} \leq 119 \text{ °C; both diodes} \\ \text{conducting; see } \underline{Figure 1;} \\ \text{see } \underline{Figure 2} \\ \\ \text{repetitive peak forward} \\ \text{current} \\ \\ \text{T}_{mb} \leq 119 \text{ °C; per diode;} \\ \text{square-wave pulse} \\ \\ \text{acteristics} \\ \\ \text{forward voltage} \\ \\ \text{I}_F = 5 \text{ A; } T_j = 150 \text{ °C;} \\ \text{see } \underline{Figure 4} \\ \\ \text{haracteristics} \\ \\ \text{reverse recovery time} \\ \\ \text{I}_F = 1 \text{ A; } V_R = 30 \text{ V;} \\ \text{dI}_F/\text{dt} = 100 \text{ A/\mu s; } T_j = 25 \text{ °C;} \\ \text{ramp recovery; see } \underline{Figure 5} \\ \\ \text{c discharge} \\ \\ \text{electrostatic discharge} \\ \\ \text{HBM; } C = 250 \text{ pF; } R = 1.5 \text{ k}\Omega; \\ \\ \text{-} \\ \\ \end{array} $	repetitive peak reverse voltage $ \begin{array}{c} \text{repetitive peak reverse} \\ \text{voltage} \end{array} \begin{array}{c} \text{-} \\ \text{average output current} \end{array} \begin{array}{c} \text{square-wave pulse; } \delta = 0.5 \ ; \\ T_{mb} \leq 119 \ ^{\circ}\text{C; both diodes} \\ \text{conducting; see } \underline{Figure 1;} \\ \text{see } \underline{Figure 2} \end{array} \\ \text{repetitive peak forward} \\ \text{current} \end{array} \begin{array}{c} \delta = 0.5 \ ; \ t_p = 25 \ \mu\text{s;} \\ T_{mb} \leq 119 \ ^{\circ}\text{C; per diode;} \\ \text{square-wave pulse} \end{array} \begin{array}{c} \text{-} \\ \text{-} \\ \text{-} \\ \text{-} \\ \text{cacteristics} \end{array} \\ \text{forward voltage} \hspace{0.5cm} I_F = 5 \ A; \ T_j = 150 \ ^{\circ}\text{C;} \\ \text{see } \underline{Figure 4} \end{array} \begin{array}{c} \text{-} \\ \text{0.8} \\ \text{see } \underline{Figure 5} \end{array} \\ \text{reverse recovery time} \hspace{0.5cm} I_F = 1 \ A; \ V_R = 30 \ V; \\ \text{dI}_F/\text{dt} = 100 \ A/\mu\text{s; } T_j = 25 \ ^{\circ}\text{C;} \\ \text{ramp recovery; see } \underline{Figure 5} \end{array} \begin{array}{c} \text{-} \\ \text{15} \\ \text{c discharge} \\ \text{electrostatic discharge} \end{array} \\ \text{HBM; } C = 250 \ \text{pF; } R = 1.5 \ \text{k}\Omega; \ \text{-} \\ \text{-} \end{array} \begin{array}{c} \text{-} \\ \text{-} \\ \text{-} \\ \text{-} \end{array}$	repetitive peak reverse voltage $ \begin{array}{ccccccccccccccccccccccccccccccccccc$



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		<u> </u>
mb	К	mounting base; cathode	1 2 3	sym125
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYQ28E-200E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage	DC	-	200	V
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5 ; $T_{mb} \le$ 119 °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	10	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; T_{mb} ≤ 119 °C; per diode; square-wave pulse	-	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	55	Α
		t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	50	Α
I _{RRM}	repetitive peak reverse current	$\delta = 0.001 \; ; \; t_p = 2 \; \mu s$	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	$t_{p} = 100 \ \mu s$	-	0.2	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Electrostation	c discharge				
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	-	8	kV

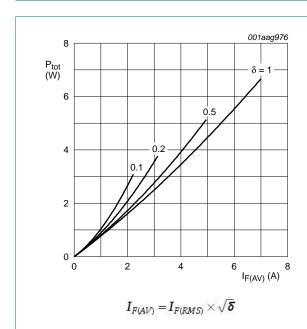
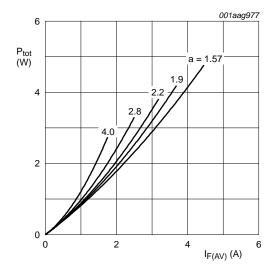


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a =form factor $= I_{F(RMS)} / I_{F(AV)}$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; both diodes conducting	-	-	3	K/W
		with heatsink compound; per diode; see Figure 3	-	-	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

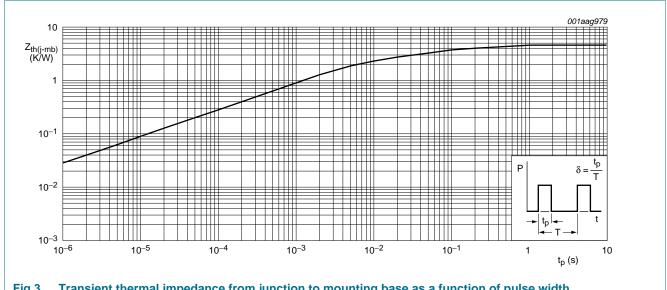


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 5 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 4	-	0.95	1.1	V
		$I_F = 5 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 4	-	8.0	0.895	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{\text{Minimum 1}}$	-	1.1	1.25	V
I _R	reverse current	$V_R = 200 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	10	μΑ
		$V_R = 200 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.2	mΑ
Dynamic o	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R \ge 30 \text{ V}$; $dI_F/dt = 20 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	4	9	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; ramp recovery; $T_j = 25 \text{ °C}$; see Figure 5	-	15	25	ns
		$I_F = 0.5 \text{ A}$; $I_R = 1 \text{ A}$; step recovery; $T_j = 25 \text{ °C}$; see Figure 6	-	10	20	ns
I _{RM}	peak reverse recovery current	$I_F = 2 \text{ A}$; $V_R \ge 30 \text{ V}$; $dI_F/dt = 20 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	0.4	0.7	Α
V_{FR}	forward recovery voltage	$I_F = 1$ A; $dI_F/dt = 10$ A/ μ s; $T_j = 25$ °C; see Figure 7	-	1	-	V

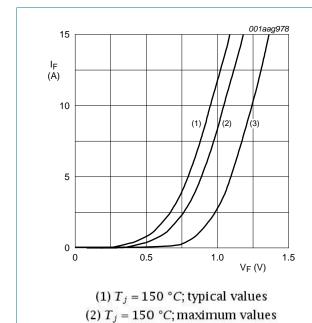


Fig 4. Forward current as a function of forward voltage

(3) $T_j = 25$ °C; maximum values

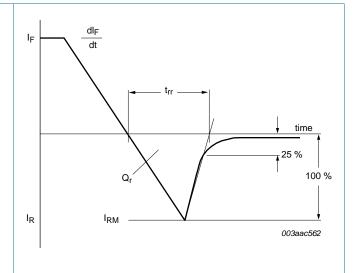
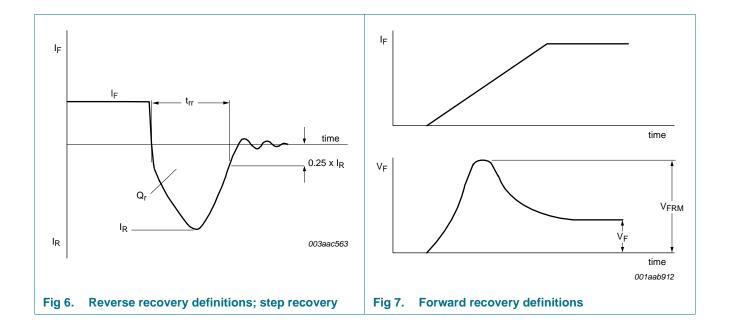


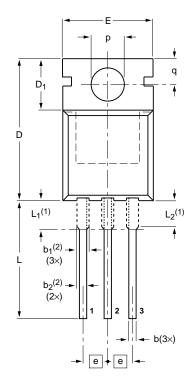
Fig 5. Reverse recovery definitions; ramp recovery

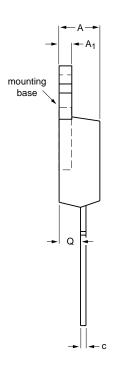


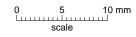
7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

ļ	TINL	A	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q	
	mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 8. Package outline SOT78 (TO-220AB)

BYQ28E-200E

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYQ28E-200E v.4	20110714	Product data sheet	-	BYQ28E_SERIES v.3
Modifications:	 The format of this guidelines of NXP 	28E-200E separated fron data sheet has been rede Semiconductors. een adapted to the new c	signed to comply with the	e new identity
BYQ28E_SERIES v.3	19981001	Product specification	-	BYQ28E_SERIES v.2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Dual ultrafast power diodes

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